





100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C
100V	220mΩ @ V _{GS} = 10V	1.6A
100 V	250mΩ @ V _{GS} = 4.5V	1.3A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMN10H220LQ</u>)

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Load Switches

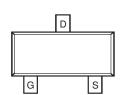
Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.0072 grams (Approximate)

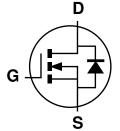




Top View



Pin Configuration



Equivalent Circuit

Ordering Information

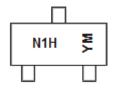
Part Number	Compliance	Packago	king	
Part Number	Compliance	Package	Qty.	Carrier
DMN10H220L-7	Standard	SOT23 (Standard)	3000	Tape & Reel
DMN10H220L-13	Standard	SOT23 (Standard)	10,000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information



N1H = Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M = \overline{M} (ex: 9 = September)

Date Code Key

Year	2013		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Α		I	J	K	L	М	N	0	Р	R	S
	•	•										
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	100	V		
Gate-Source Voltage			V _{GSS}	±16	V
Ocationary Davis Ocasat (Note EV)		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	1.6 1.3	А
Continuous Drain Current (Note 5) V _{GS} = 10V	(Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	1.4 1.1	А
Maximum Continuous Body Diode Forward Currer	t (Note 6)	Is	0.6	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%)		I _{DM}	8	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	6	1.3	W	
Total Fower Dissipation (Note 6)	$T_A = +70^{\circ}C$	P _D	0.8	VV	
Thermal Resistance, Junction to Ambient	(Note 6)	Г	94	°C/W	
Thermal nesistance, junction to Ambient	(Note 5)	$R_{\Theta JA}$	177	C/VV	
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C	

Notes:

^{5.} Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.



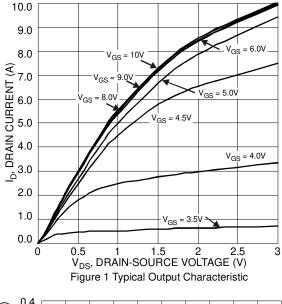
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

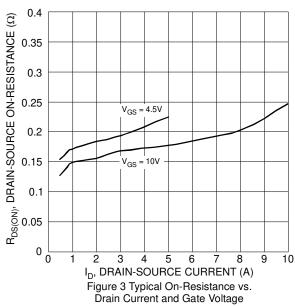
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 100V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance			160	220	mΩ	$V_{GS} = 10V, I_D = 1.6A$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	190	250	11177	$V_{GS} = 4.5V, I_D = 1.3A$
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 1.1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	1	401	_		V 05V V 0V
Output Capacitance	Coss		22	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz
Reverse Transfer Capacitance	C _{rss}		17	_		1 = 1101112
Gate Resistance	R_g	_	2.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	4.1	_		
Total Gate Charge (V _{GS} = 10V)	Qg		8.3	_	nC	V 50V L 16A
Gate-Source Charge	Q_{gs}	_	1.5	_	110	$V_{DS} = 50V, I_D = 1.6A$
Gate-Drain Charge	Q_{gd}	_	2	_		
Turn-On Delay Time	t _{D(on)}	_	6.8	_		
Turn-On Rise Time	t _r		8.2	_		$V_{DS} = 50V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(off)}	_	7.9	_	ns	$R_G = 6.8\Omega$, $I_D = 1A$
Turn-Off Fall Time	t _f		3.6	_		
Reverse Recovery Time	t _{rr}		17	_	ns	1 4 4 8 -11/-14 4 4 0 0 8 /
Reverse Recovery Charge	Q_{rr}		9.8	_	nC	I _F = 1.1A, di/dt =100A/μs

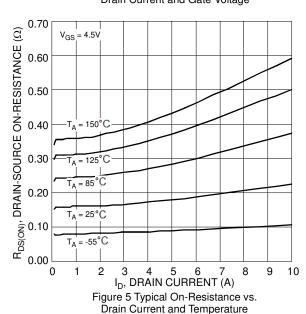
Notes:

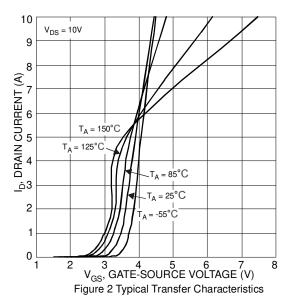
^{7 .}Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.

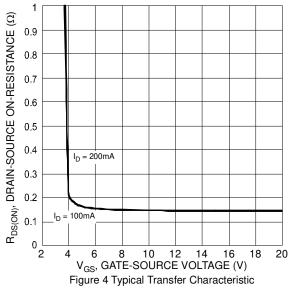












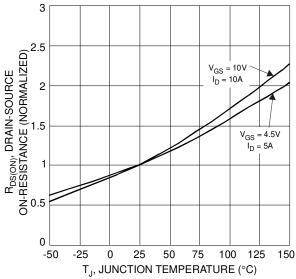
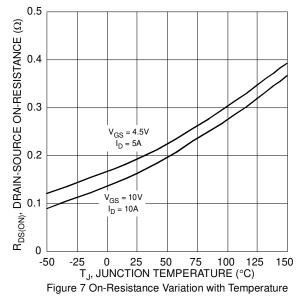
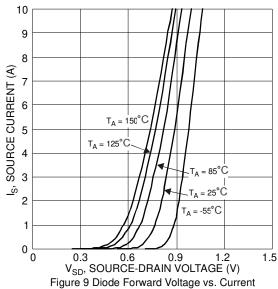
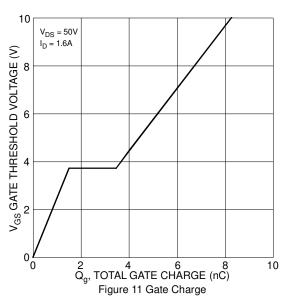


Figure 6 On-Resistance Variation with Temperature









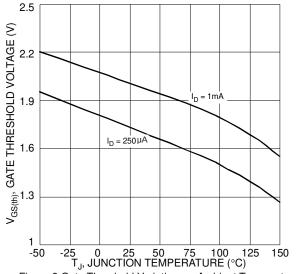
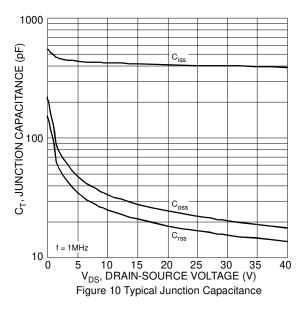
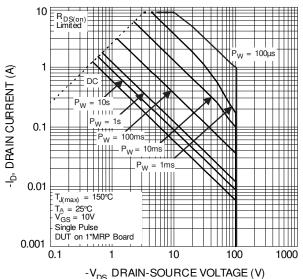


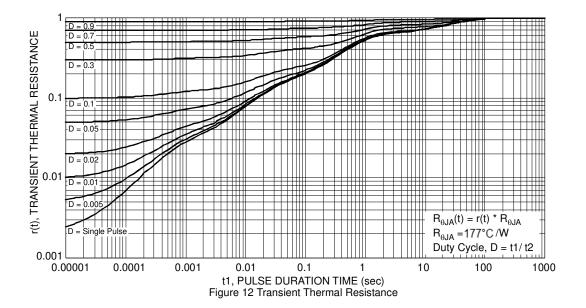
Figure 8 Gate Threshold Variation vs. Ambient Temperature





 ${}^{-}\mathrm{V}_{\mathrm{DS}}$ DRAIN-SOURCE VOLTAGE (V) Figure 12 SOA, Safe Operation Area

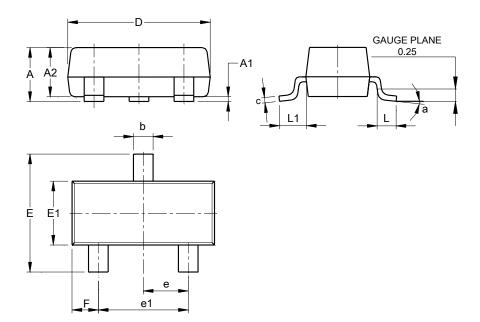






Package Outline Dimensions

Please see https://www.diodes.com/design/support/packaging/diodes-packaging/ for the latest version.

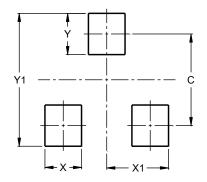


SOT23 (Standard)							
Dim	Min	Min Max					
Α	0.90	1.15	1.025				
A1	0.00	0.10	0.05				
A2	0.85	1.10	0.975				
b	0.30	0.51	0.40				
С	0.080	0.202	0.11				
D	2.80	3.00	2.90				
Е	2.25	2.55	2.40				
E1	1.20	1.40	1.30				
е	0.89	1.03	0.915				
e1	1.78	2.05	1.83				
F	0.40	0.60	0.535				
L1	0.45	0.61	0.55				
L	0.25	0.55	0.40				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

 $Please see \ https://www.diodes.com/design/support/packaging/diodes-packaging/ for the \ latest \ version.$

SOT23 (Standard)



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Υ	0.9
Y1	2.9



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